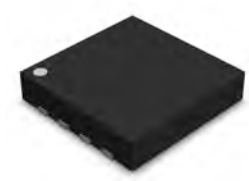
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

DFNWB3×3-8L Plastic-Encapsulate MOSFETS

CJAE55P03 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$TYP	I_D
-30V	8.0mΩ@-10V	-55A
	11.5mΩ@-4.5V	

DFNWB3×3-8L



DESCRIPTION

The CJAE55P03 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

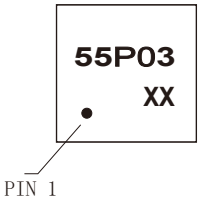
FEATURES

- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

- Battery and loading switching

MARKING

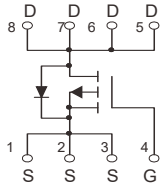


55P03 = Part No.

Solid dot=Pin1 indicator.

XX=Code.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D ①	-55	A
Pulsed Drain Current	I_{DM} ②	-200	A
Single Pulsed Avalanche Energy	E_{AS} ③	150	mJ
Power Dissipation	P_D ①	50	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$ ⑥	83.3	℃/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$ ①	2.5	℃/W
Operating Junction and Storage Temperature Range	T_J ,T_{stg}	-55~+150	℃

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA		-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V, V_{GS} =0V	T_J =25℃			-1	μA
			T_J =125℃			-100	
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V				±100	nA
On characteristics ④							
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA		-1.0	-1.6	-2.5	V
Static drain-source on-sate resistance	$R_{DS(on)}$	V_{GS} =-10V, I_D =-10A			8.0	10.0	mΩ
		V_{GS} =-4.5V, I_D =-8A			11.5	15.0	mΩ
Forward transconductance	g_{FS}	V_{DS} =-10V, I_D =-8A			16		S
Dynamic characteristics ④⑤							
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V, f =1MHz			3282	5900	pF
Output capacitance	C_{oss}				413	830	
Reverse transfer capacitance	C_{rss}				273	550	
Switching characteristics ④⑤							
Total gate charge	Q_g	V_{GS}=-4.5V, V_{DS}=-15V, I_D=-10A			34.3	60	nC
Gate-source charge	Q_{gs}				11	19	
Gate-drain charge	Q_{gd}				10	18	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V,I_D=-1A, V_{GS}=-10V,R_G=6Ω			25	42	ns
Turn-on rise time	t_r				11	22	
Turn-off delay time	$t_{d(off)}$				136	250	
Turn-off fall time	t_f				49	82	
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V_{SD} ④	V_{GS} =0V, I_S=-10A				-1.2	V
Continuous drain-source diode forward current	I_S ①					-55	A
Pulsed drain-source diode forward current	I_{SM} ②					-200	A

Notes:

1.T_C=25℃ Limited only by maximum temperature allowed.

2.P_W≤10μs, Duty cycle≤1%.

3.EAS condition: V_{DD}=-15V,V_{GS}=-10V, L=0.5mH, Rg=25Ω Starting T_J= 25°℃.

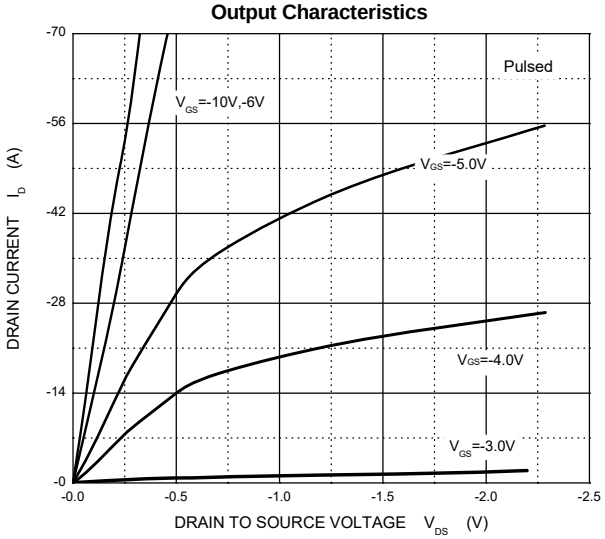
4.Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.

5.Guaranteed by design, not subject to production.

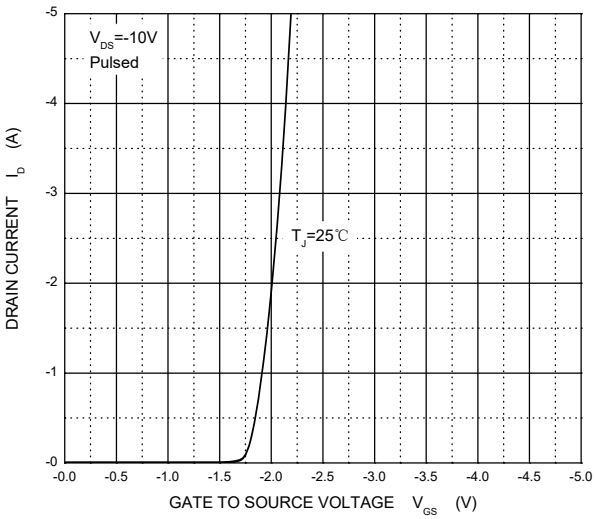
6.The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25℃.

Typical Characteristics

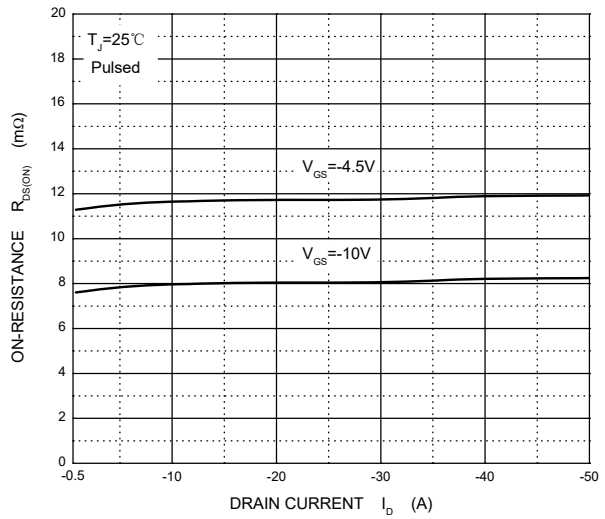
Output Characteristics



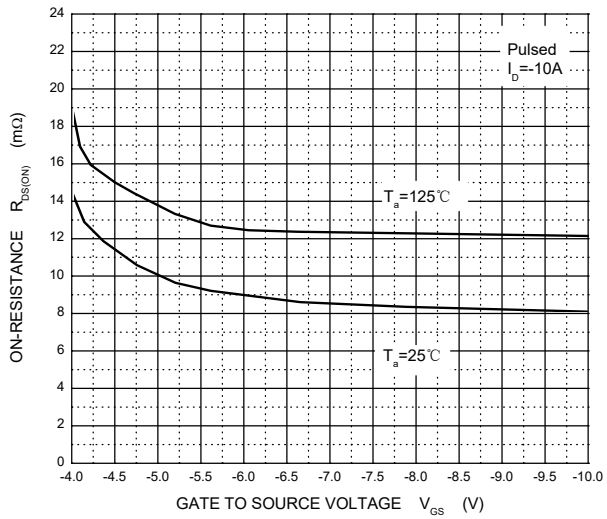
Transfer Characteristics



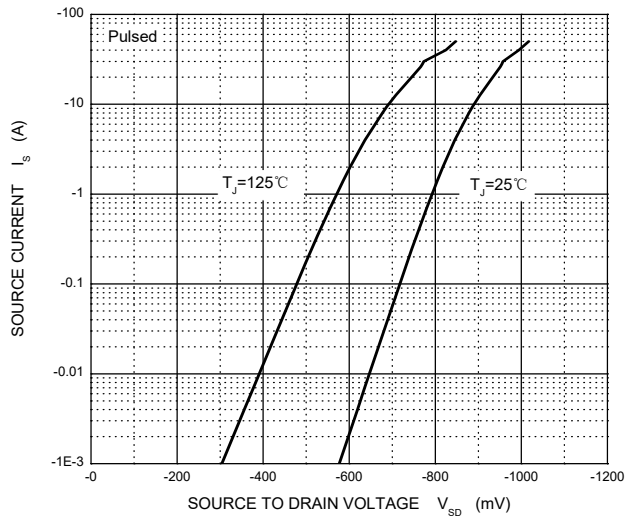
$R_{DS(ON)}$ —— I_D



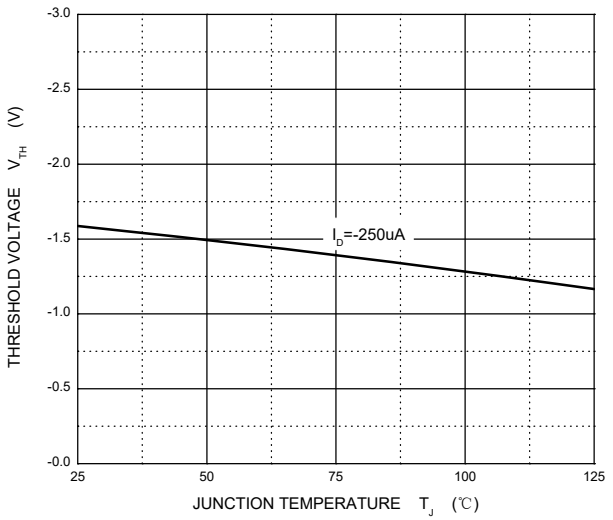
$R_{DS(ON)}$ —— V_{GS}



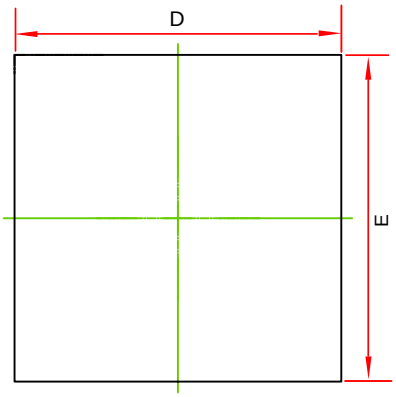
I_S —— V_{SD}



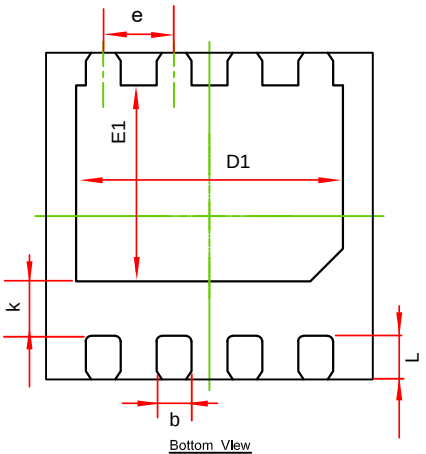
Threshold Voltage



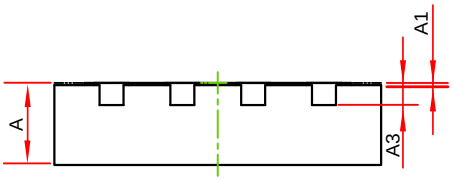
DFNWB3×3-8L Package Outline Dimensions



Top View
[顶视图]



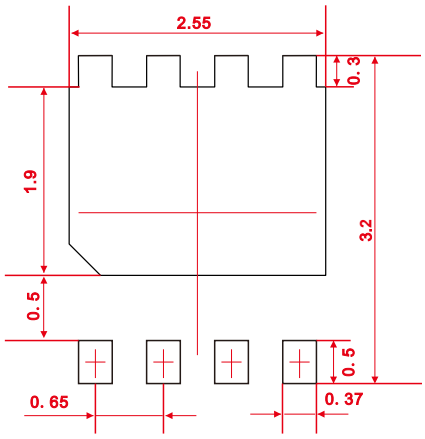
Bottom View
[背视图]



Side View
[侧视图]

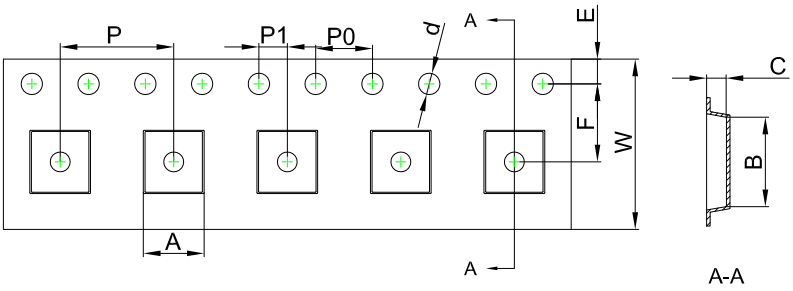
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203 REF.		0.008 REF.	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.350	2.550	0.093	0.100
E1	1.700	1.900	0.067	0.075
k	0.200 MIN.		0.008MIN.	
b	0.270	0.370	0.011	0.015
e	0.650 TYP.		0.026 TYP.	
L	0.300	0.500	0.012	0.020

DFNWB3×3-8L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

DFNWB3×3-8L Embossed Carrier Tape

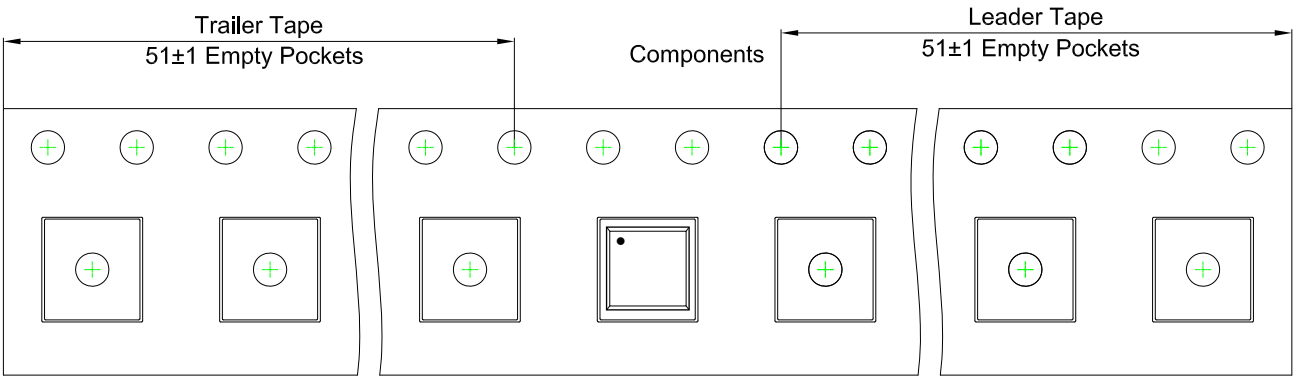


Packaging Description:

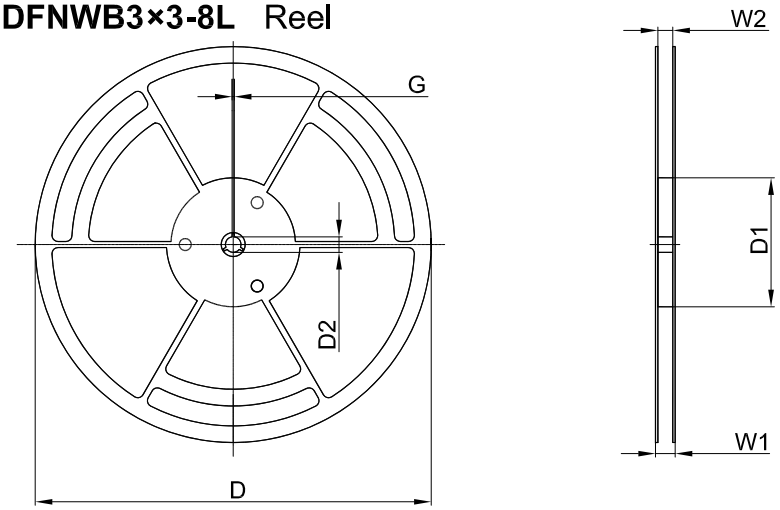
DFNWB3x3-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
DFNWB3×3-8L	3.35	3.35	1.13	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

DFNWB3×3-8L Tape Leader and Trailer



DFNWB3×3-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	10,000 pcs	360×360×65	50,000 pcs	378×358×382